IN THE CLAIMS

1-24. (Canceled).

25. (Previously Presented) A method of manufacturing a semiconductor integrated circuit device comprising the steps of:

(a) holding a semiconductor wafer in a state in which circuit elements and a plurality of electrodes connected to the circuit elements through first wirings are formed in a plurality of chip areas of a major surface of the semiconductor wafer, respectively;

(b) forming an insulating layer on the circuit elements and the plurality of electrodes after a product type is fixed, selectively forming a second wiring on the insulating layer. and connecting the second wiring to a predetermined electrode of the plurality of electrodes to select a function or a characteristic depending on the fixed product type; and

(c) cutting the semiconductor wafer in units of the chip areas to obtain a plurality of semiconductor chips.

26. (Previously Presented) A method of manufacturing a semiconductor integrated circuit device according to claim 25, comprising the step of forming an external connection terminal connected to the second wiring after the step (b) prior to the step (c).

27. (Previously Presented) A method of manufacturing a semiconductor integrated circuit device according to claim 25, wherein the insulating layer is formed by an organic insulating layer.

28. (Previously Presented) A method of manufacturing a semiconductor integrated circuit device according to claim 27, wherein the organic insulating layer includes an elastomer layer.

29. (Currently Amended) A method of manufacturing a semiconductor integrated circuit device, ~~according to claim 25~~ comprising the steps of:

(a) holding a semiconductor wafer in a state in which circuit elements and a plurality of electrodes connected

to the circuit elements through first wirings are formed in a plurality of chip areas of a major surface of the semiconductor wafer, respectively;

(b) forming an insulating layer on the circuit elements and the plurality of electrodes after a product type is fixed, selectively forming a second wiring on the insulating layer. and connecting the second wiring to a predetermined electrode of the plurality of electrodes to select a function or a characteristic depending on the fixed product type; and

(c) cutting the semiconductor wafer in units of the chip areas to obtain a plurality of semiconductor chips,

wherein in the step (b), an alignment pattern formed of the same material as that of the second wiring is formed on the insulating layer.

30. (Currently Amended) A method of manufacturing a semiconductor integrated circuit device, ~~according to claim 25~~ comprising the steps of:

(a) holding a semiconductor wafer in a state in which circuit elements and a plurality of electrodes connected

to the circuit elements through first wirings are formed in a plurality of chip areas of a major surface of the semiconductor wafer, respectively;

(b) forming an insulating layer on the circuit elements and the plurality of electrodes after a product type is fixed, selectively forming a second wiring on the insulating layer. and connecting the second wiring to a predetermined electrode of the plurality of electrodes to select a function or a characteristic depending on the fixed product type; and

(c) cutting the semiconductor wafer in units of the chip areas to obtain a plurality of semiconductor chips,

wherein in the step (b), a product information pattern formed of the same material as that of the second wiring is formed on the insulating layer.

31. (Previously Presented) A method of manufacturing a semiconductor integrated circuit device according to claim 25, wherein the function corresponding to the fixed product type is a bit configuration or an operation mode, a characteristic corresponding to the fixed product type is an output impedance, at operation voltage, or a slew rate.